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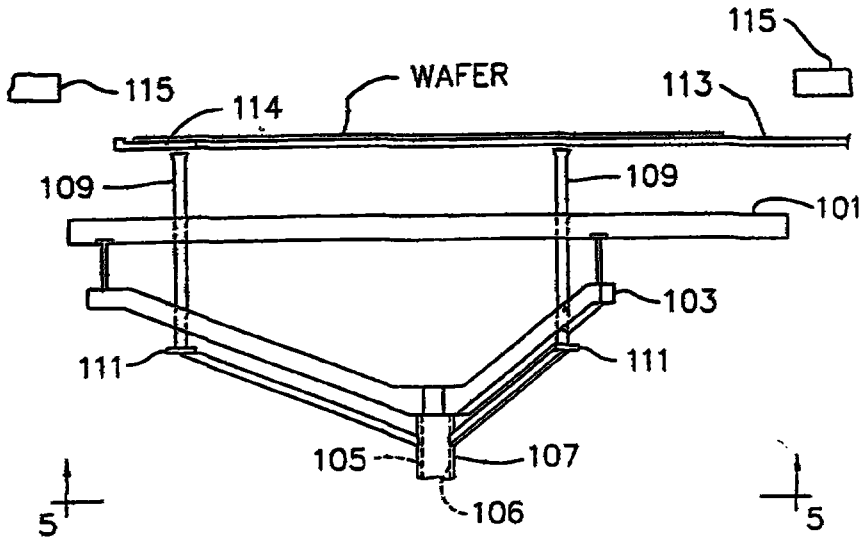
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(54) Title: A METHOD FOR THE PREPARATION OF AN EPITAXIAL SILICON WAFER WITH INTRINSIC GETTERING



(57) Abstract: This invention is directed to a novel process for the preparation of a silicon wafer comprising a surface having an epitaxial layer deposited thereon. In one embodiment, an epitaxial layer is deposited onto a surface of a silicon wafer. The wafer is also heated to a temperature of at least about 1175 °C. This heat treatment begins either during or after the epitaxial deposition. Following the heat treatment, the heated wafer is cooled for a period of time at a rate of at least about 10 °C/sec while (a) the temperature of the wafer is greater than about 1000 °C, and (b) the wafer is not in contact with a susceptor. In this process, the epitaxial deposition, heating, and cooling are conducted in the same reactor chamber.

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